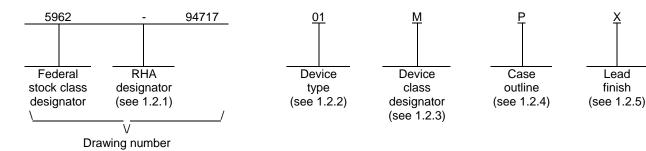
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MICROCIRCUIT DRAWING			Jeff Bowling				http://www.dscc.dla.mil													
THIS DRAWING IS AVAILABLE FOR USE BY ALL DEPARTMENTS			APPROVED BY Michael A. Frye				MICROCIRCUIT, MEMORY, DIGITAL, CMOS 64K X 1-BIT SERIAL CONFIGURATION PRO													
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1. SCOPE

- 1.1 <u>Scope</u>. This drawing documents two product assurance class levels consisting of high reliability (device classes Q and M) and space application (device class V). A choice of case outlines and lead finishes are available and are reflected in the Part or Identifying Number (PIN). When available, a choice of Radiation Hardness Assurance (RHA) levels are reflected in the PIN.
 - 1.2 PIN. The PIN is as shown in the following example:



- 1.2.1 <u>RHA designator</u>. Device classes Q and V RHA marked devices meet the MIL-PRF-38535 specified RHA levels and are marked with the appropriate RHA designator. Device class M RHA marked devices meet the MIL-PRF-38535, appendix A specified RHA levels and are marked with the appropriate RHA designator. A dash (-) indicates a non-RHA device.
 - 1.2.2 Device type(s). The device type(s) identify the circuit function as follows:

Device type	Generic number	<u>Circuit function</u>
01	1765D	64K X 1-bit PROM

1.2.3 <u>Device class designator</u>. The device class designator is a single letter identifying the product assurance level as follows:

Device class Device requirements documentation

M Vendor self-certification to the requirements for MIL-STD-883 compliant, non-

JAN class level B microcircuits in accordance with MIL-PRF-38535, appendix A

Q or V Certification and qualification to MIL-PRF-38535

1.2.4 Case outline(s). The case outline(s) are as designated in MIL-STD-1835 and as follows:

Outline letter	Descriptive designator	<u>Terminals</u>	Package style
Р	GDIP1-T8 or CDIP2-T8	8	Dual-in-line package

1.2.5 <u>Lead finish</u>. The lead finish is as specified in MIL-PRF-38535 for device classes Q and V or MIL-PRF-38535, appendix A for device class M.

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1.3 Absolute maximum ratings. 1/

Supply voltage range to ground potential (V _{CC})	-0.5 V dc to +7.0 V dc
Input voltage with respect to ground	$-0.5 \text{ V dc to V}_{CC} + 0.5 \text{ V dc}$
Voltage applied to three state output	$-0.5 \text{ V dc to V}_{CC} + 0.5 \text{ V dc}$
Lead temperature (soldering, 10 seconds)	+260°C
Thermal resistance, junction-to-case (θ_{JC})	See MIL-STD-1835
Junction temperature (T _J)	+150°C
Storage temperature range (T _{STG})	-65°C to +150°C
Data retention	

1.4 Recommended operating conditions.

Supply voltage range (V _{CC})	+4.5 V dc minimum to +5.5 V dc maximum
Ground voltage (GND)	0 V dc
Input high voltage (V _{IH})	2.0 V dc to V _{CC}
Input low voltage (V _{IL})	0 V dc to 0.8 V dc
Case operating temperature range (T _C)	-55°C to +125°C

2. APPLICABLE DOCUMENTS

2.1 <u>Government specification, standards, and handbooks</u>. The following specification, standards, and handbooks form a part of this drawing to the extent specified herein. Unless otherwise specified, the issues of these documents are those cited in the solicitation or contract.

DEPARTMENT OF DEFENSE SPECIFICATION

MIL-PRF-38535 - Integrated Circuits, Manufacturing, General Specification for.

DEPARTMENT OF DEFENSE STANDARDS

MIL-STD-883 - Test Method Standard Microcircuits.

MIL-STD-1835 - Interface Standard Electronic Component Case Outlines.

DEPARTMENT OF DEFENSE HANDBOOKS

MIL-HDBK-103 - List of Standard Microcircuit Drawings.
MIL-HDBK-780 - Standard Microcircuit Drawings.

(Copies of these documents are available online at http://assist.daps.dla.mil/quicksearch/ or http://assist.daps.dla.mil or from the Standardization Document Order Desk, 700 Robbins Avenue, Building 4D, Philadelphia, PA 19111-5094.)

Stresses above the absolute maximum rating may cause permanent damage to the device. Extended operation at the maximum levels may degrade performance and affect reliability.

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2.2 <u>Non-Government publications</u>. The following documents form a part of this document to the extent specified herein. Unless otherwise specified, the issues of the documents are the issues of the documents cited in the solicitation.

ELECTRONIC INDUSTRIES ALLIANCE (EIA)

JEDEC Standard EIA/JESD 78 - IC Latch-Up Test.

(Applications for copies should be addressed to the Electronics Industries Association, 2500 Wilson Boulevard, Arlington, VA 22201; http://www.jedec.org.)

(Non-Government standards and other publications are normally available from the organizations that prepare or distribute the documents. These documents also may be available in or through libraries or other informational services.)

2.3 <u>Order of precedence</u>. In the event of a conflict between the text of this drawing and the references cited herein, the text of this drawing takes precedence. Nothing in this document, however, supersedes applicable laws and regulations unless a specific exemption has been obtained.

3. REQUIREMENTS

- 3.1 <u>Item requirements</u>. The individual item requirements for device classes Q and V shall be in accordance with MIL-PRF-38535 and as specified herein or as modified in the device manufacturer's Quality Management (QM) plan. The modification in the QM plan shall not affect the form, fit, or function as described herein. The individual item requirements for device class M shall be in accordance with MIL-PRF-38535, appendix A for non-JAN class level B devices and as specified herein.
- 3.2 <u>Design, construction, and physical dimensions</u>. The design, construction, and physical dimensions shall be as specified in MIL-PRF-38535 and herein for device classes Q and V or MIL-PRF-38535, appendix A and herein for device class M.
 - 3.2.1 <u>Case outline</u>. The case outline shall be in accordance with 1.2.4 herein.
 - 3.2.2 Terminal connections. The terminal connections shall be as specified on figure 1.
 - 3.2.3 Truth table. The truth table shall be as specified on figure 2.
- 3.2.3.1 <u>Unprogrammed devices</u>. The truth table for unprogrammed devices for contracts involving no altered item drawing shall be as specified on figure 2. When required in screening (see 4.2 herein) or qualification conformance inspection, groups A, B, or C (see 4.4), the devices shall be programmed by the manufacturer prior to test. A minimum of 50 percent of the total number of cells shall be programmed or at least 25 percent of the total number of cells to any altered item drawing.
- 3.2.3.2 <u>Programmed devices</u>. The truth table for programmed devices shall be as specified by an attached altered item drawing.
- 3.3 <u>Electrical performance characteristics and postirradiation parameter limits</u>. Unless otherwise specified herein, the electrical performance characteristics and postirradiation parameter limits are as specified in table I and shall apply over the full case operating temperature range.
- 3.4 <u>Electrical test requirements</u>. The electrical test requirements shall be the subgroups specified in table IIA. The electrical tests for each subgroup are defined in table I.
- 3.5 <u>Marking</u>. The part shall be marked with the PIN listed in 1.2 herein. In addition, the manufacturer's PIN may also be marked. For packages where marking of the entire SMD PIN number is not feasible due to space limitations, the manufacturer has the option of not marking the "5962-" on the device. For RHA product using this option, the RHA designator shall still be marked. Marking for device classes Q and V shall be in accordance with MIL-PRF-38535. Marking for device class M shall be in accordance with MIL-PRF-38535, appendix A.
- 3.5.1 <u>Certification/compliance mark</u>. The certification mark for device classes Q and V shall be a "QML" or "Q" as required in MIL-PRF-38535. The compliance mark for device class M shall be a "C" as required in MIL-PRF-38535, appendix A.

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- 3.6 <u>Certificate of compliance</u>. For device classes Q and V, a certificate of compliance shall be required from a QML-38535 listed manufacturer in order to supply to the requirements of this drawing (see 6.6.1 herein). For device class M, a certificate of compliance shall be required from a manufacturer in order to be listed as an approved source of supply in MIL-HDBK-103 (see 6.6.2 herein). The certificate of compliance submitted to DSCC-VA prior to listing as an approved source of supply for this drawing shall affirm that the manufacturer's product meets, for device classes Q and V, the requirements of MIL-PRF-38535 and herein or for device class M, the requirements of MIL-PRF-38535, appendix A and herein.
- 3.7 <u>Certificate of conformance</u>. A certificate of conformance as required for device classes Q and V in MIL-PRF-38535 or for device class M in MIL-PRF-38535, appendix A shall be provided with each lot of microcircuits delivered to this drawing.
- 3.8 <u>Notification of change for device class M</u>. For device class M, notification to DSCC-VA of change of product (see 6.2 herein) involving devices acquired to this drawing is required for any change that affects this drawing.
- 3.9 <u>Verification and review for device class M.</u> For device class M, DSCC, DSCC's agent, and the acquiring activity retain the option to review the manufacturer's facility and applicable required documentation. Offshore documentation shall be made available onshore at the option of the reviewer.
- 3.10 <u>Microcircuit group assignment for device class M</u>. Device class M devices covered by this drawing shall be in microcircuit group number 42 (see MIL-PRF-38535, appendix A).
- 3.11 <u>Data retention</u>. A data retention stress test shall be completed as part of the vendor's reliability monitors. This test shall be done for initial characterization and after any design or process changes which may affect data retention. The methods and procedures may be vendor specific, but shall guarantee the number of years listed in section 1.3 herein over the full military temperature range. The vendor's procedure shall be kept under document control and shall be made available upon request of the acquiring or preparing activity, along with test data.

4. VERIFICATION

- 4.1 <u>Sampling and inspection</u>. For device classes Q and V, sampling and inspection procedures shall be in accordance with MIL-PRF-38535 or as modified in the device manufacturer's Quality Management (QM) plan. The modification in the QM plan shall not affect the form, fit, or function as described herein. For device class M, sampling and inspection procedures shall be in accordance with MIL-PRF-38535, appendix A.
- 4.2 <u>Screening</u>. For device classes Q and V, screening shall be in accordance with MIL-PRF-38535, and shall be conducted on all devices prior to qualification and technology conformance inspection. For device class M, screening shall be in accordance with method 5004 of MIL-STD-883, and shall be conducted on all devices prior to quality conformance inspection.
 - 4.2.1 Additional criteria for device class M.
 - a. Burn-in test, method 1015 of MIL-STD-883.
 - (1) Test condition D. The test circuit shall be maintained by the manufacturer under document revision level control and shall be made available to the preparing or acquiring activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in method 1015.
 - (2) $T_A = +125^{\circ}C$, minimum.
 - b. Interim and final electrical test parameters shall be as specified in table IIA herein.
 - 4.2.2 Additional criteria for device classes Q and V.
 - a. The burn-in test duration, test condition and test temperature, or approved alternatives shall be as specified in the device manufacturer's QM plan in accordance with MIL-PRF-38535. The burn-in test circuit shall be maintained under document revision level control of the device manufacturer's Technology Review Board (TRB) in accordance with MIL-PRF-38535 and shall be made available to the acquiring or preparing activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in method 1015 of MIL-STD-883.
 - b. Interim and final electrical test parameters shall be as specified in table IIA herein.
 - Additional screening for device class V beyond the requirements of device class Q shall be as specified in MIL-PRF-38535, appendix B.

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TABLE I. Electrical performance characteristics.

Test	Symbol	Conditions $-55^{\circ}C \le T_{C} \le +125^{\circ}C$ $4.5 \text{ V} \le V_{CC} \le 5.5 \text{ V}$	Group A subgroups	Lim	Unit	
		unless otherwise specified		Min	Max	
Power supply current	I _{CC}	CLK = Max	1, 2, 3		10	mA
Standby current	I _{SB}		1, 2, 3		1.5	mA
Input leakage current	I _{IL}	$V_{IN} = GND \text{ or } V_{CC}$	1, 2, 3		±10	μΑ
Output leakage current	I _{OZ}	V _{OUT} = GND or V _{CC}	1, 2, 3		±10	μΑ
Input low voltage	V _{IL}		1, 2, 3	0	0.8	V
Input high voltage	V _{IH}		1, 2, 3	2.0	V _{CC}	V
Output low voltage	V _{OL}	I _{OL} = 4 mA	1, 2, 3		0.4	V
Output high voltage	V _{OH}	I _{OH} = -4 mA	1, 2, 3	3.7		V
Output capacitance	C _{OUT}	f = 1.0 MHz, V _{OUT} = 0 V see 4.4.1c <u>1</u> /	4		10	pF
Input capacitance	C _{IN}	f = 1.0 MHz, V _{IN} = 0 V see 4.4.1c <u>1</u> /	4		10	pF
Functional tests		see 4.4.1d	7, 8A, 8B			
Clock frequency	f _{CK}	See figures 3 and 4 as applicable.	9, 10, 11		5	MHz
Clock period	t _{CK}		9, 10, 11	200		ns
CLK low time 2/	t _{LC}		9, 10, 11	100		ns
CLK high time 2/	t _{HC}		9, 10, 11	100		ns

See footnotes at end of table.

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TABLE I. <u>Electrical performance characteristics</u> – Continued.

Test	Symbol	Conditions $-55^{\circ}C \le T_{C} \le +125^{\circ}C$ $4.5 \text{ V} \le V_{CC} \le 5.5 \text{ V}$	Group A subgroups	Lin	nits	Unit
		unless otherwise specified		Min	Max	
OE to data delay	t _{OE}	See figures 3 and 4 as applicable.	9, 10, 11		45	ns
CE to data delay	t _{CE}		9, 10, 11		60	ns
CE or OE to data	t _{DF}		9, 10, 11		50	ns
CE setup time to CLK	t _{SCE}		9, 10, 11	25		ns
CE hold time to CLK	t _{HCE}		9, 10, 11	0		ns
Data hold time from CE, OE, or CLK	t _{OH}		9, 10, 11	0		ns
CLK to data delay	t _{CAC}		9, 10, 11		150	ns
OE high time	t _{HOE}		9, 10, 11	100		ms
CLK to CEO delay	t _{OCK}		9, 10, 11		65	ns
CLK to data float delay 3/	t _{CDF}		9, 10, 11		50	ns
CE to CEO delay	t _{OCE}		9, 10, 11		45	ns
RESET/OE to CEO delay	t _{OOE}		9, 10, 11		40	ns

- C_{IN} and C_{OUT} are periodically sampled and not 100-percent tested but shall be guaranteed to the limits specified in table I. These parameters are guaranteed by periodic characterization. Float delays are measured with minimum tester a. c. load and maximum d. c. load.

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Device type 01		
Case	outline P	
Terminal number	Terminal symbol	
1	DATA	
2	CLK	
3	RESET/OE or	
	RESET /OE	
4	CE	
5 GND		
6	CEO	
7 V _{PP}		
8	V _{cc}	

FIGURE 1. <u>Terminal connections</u>.

RESET	CE	DATA	CEO	COMMENTS
Inactive	L	D _{OUT}	Н	If address < TC
Inactive	L	Hi-Z	L	If address > TC
Inactive	Н	Hi-Z	Н	
Active	Х	Hi-Z	Н	X = don't care

FIGURE 2. Truth table.

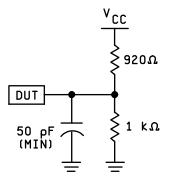
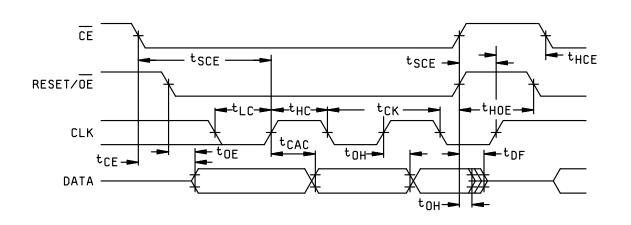


FIGURE 3. Output load circuit and test conditions.

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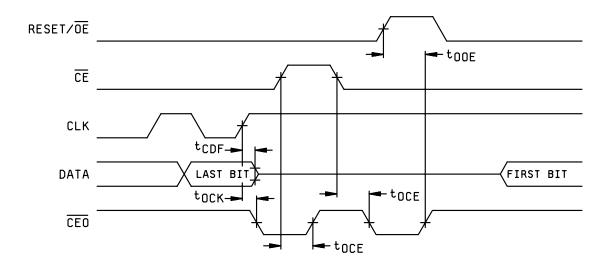


FIGURE 4. Switching waveform.

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- 4.3 <u>Qualification inspection for device classes Q and V</u>. Qualification inspection for device classes Q and V shall be in accordance with MIL-PRF-38535. Inspections to be performed shall be those specified in MIL-PRF-38535 and herein for groups A, B, C, D, and E inspections (see 4.4.1 through 4.4.4).
- 4.4 <u>Conformance inspection</u>. Technology conformance inspection for classes Q and V shall be in accordance with MIL-PRF-38535 including groups A, B, C, D, and E inspections and as specified herein. Quality conformance inspection for device class M shall be in accordance with MIL-PRF-38535, appendix A and as specified herein. Inspections to be performed for device class M shall be those specified in method 5005 of MIL-STD-883 and herein for groups A, B, C, D, and E inspections (see 4.4.1 through 4.4.4).

4.4.1 Group A inspection.

- a. Tests shall be as specified in table IIA herein.
- b. Subgroups 5 and 6 in table I, method 5005 of MIL-STD-883 shall be omitted.
- c. Subgroup 4 (C_{IN} and C_{OUT} measurements) shall be measured only for initial qualification and after any process or design changes which may affect input or output capacitance. Capacitance shall be measured between the designated terminal and GND at a frequency of 1 MHz. Sample size is 15 devices with no failures, and all input and output terminals tested.
- d. For device class M, subgroups 7 and 8 tests shall be sufficient to verify the truth table. For device classes Q and V, subgroups 7 and 8 shall include verifying the functionality of the device.
- e. O/V (latch-up) tests shall be measured only for initial qualification and after any design or process changes which may affect the performance of the device. For device class M, procedures and circuits shall be maintained under document revision level control by the manufacturer and shall be made available to the preparing activity or acquiring activity upon request. For device classes Q and V, the procedures and circuits shall be under the control of the device manufacturer's TRB in accordance with MIL-PRF-38535 and shall be made available to the preparing activity or acquiring activity upon request. Testing shall be on all pins, on five devices with zero failures. Latch-up test shall be considered destructive. Information contained in JEDEC Standard EIA/JESD 78 may be used for reference.
- f. Devices shall be tested for programmability and ac performance compliance to the requirements of group A, subgroups 9, 10, and 11. Either of two techniques is acceptable:
 - (1) Testing all devices submitted for test using additional built-in test circuitry which allows the manufacturer to verify programmability and ac performance without programming the user array. If this is done, the resulting test patterns shall be verified on all devices during subgroups 9, 10, and 11, group A testing in accordance with the sampling plan specified in MIL-STD-883, method 5005.
 - (2) If such compliance cannot be tested on an unprogrammed device, all samples submitted for testing shall be programmed in accordance with 3.2.3.1 or 3.2.3.2, as applicable. After completion of all testing, the devices shall be erased and verified except those devices submitted to groups C and D testing.
- g. Subgroups 7 and 8 shall include verification of the pattern specified in 4.4.1f.
- 4.4.2 Group C inspection. The group C inspection end-point electrical parameters shall be as specified in table IIA herein.
- 4.4.2.1 Additional criteria for device class M. Steady-state life test conditions, method 1005 of MIL-STD-883:
 - a. Test condition D. The test circuit shall be maintained by the manufacturer under document revision level control and shall be made available to the preparing or acquiring activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in method 1005 of MIL-STD-883.
 - b. $T_A = +125$ °C, minimum.
 - c. Test duration: 1,000 hours, except as permitted by method 1005 of MIL-STD-883.

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TABLE IIA. Electrical test requirements. 1/ 2/ 3/ 4/ 5/ 6/ 7/ 8/

Line no.	Test requirements	Subgroups (in accordance with MIL-STD-883, method 5005, table I)	Subgroups (per MIL-PRF-38535, table III)	
		Device class M	Device class Q	Device class V
1	Interim electrical parameters (see 4.2)	Class IVI	Class Q	1, 7, 9 or 2, 8A, 10
2	Static burn-in I and II (method 1015)	Required	Not required	Not required
3	Same as line 1			1*, 7* Δ
4	Dynamic burn-in (method 1015)	Not required	Required	Required
5	Same as line 1	•		1*, 7* Δ
6	Final electrical parameters	1*, 2, 3, 7*, 8A, 8B, 9, 10, 11	1*, 2, 3, 7*, 8A, 8B, 9, 10, 11	1*, 2, 3, 7*, 8A, 8B, 9, 10, 11
7	Group A test requirements	1, 2, 3, 4**, 7, 8A, 8B, 9, 10, 11	1, 2, 3, 4**, 7, 8A, 8B, 9, 10, 11	1, 2, 3, 4**, 7, 8A, 8B, 9, 10, 11
8	Group C end-point electrical parameters	2, 8A, 10	2, 8A, 10	1, 2, 3, 7, 8A, 8B, 9, 10, 11 Δ
9	Group D end-point electrical parameters	2, 8A, 10	2, 8A, 10	2, 3, 7, 8A, 8B
10	Group E end-point electrical parameters	1, 7, 9	1, 7, 9	1, 7, 9

- 1/ Blank spaces indicate tests are not applicable.
- 2/ Any or all subgroups may be combined when using high-speed testers.
- 3/ Subgroups 7 and 8 functional tests shall verify the truth table.
- 4/ * indicates PDA applies to subgroup 1 and 7.
- $\frac{\overline{5}}{}$ / ** see 4.4.1c.
- 6/ \(\Delta \) indicates delta limit (see table IIB) shall be required where specified, and the delta values shall be computed with reference to the previous interim electrical parameters (see line 1).
- 7/ See 4.4.1e.
- 8/ See 4.7

TABLE IIB. Delta limits at +25°C.

Test <u>1</u> /	All device types
I _{IL}	±10% of specified
	value in table I
l _{oz}	±10% of specified
	value in table I

1/ The above parameters shall be recorded before and after the required burn-in and life tests to determine the delta.

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- 4.4.2.2 Additional criteria for device classes Q and V. The steady-state life test duration, test condition and test temperature, or approved alternatives shall be as specified in the device manufacturer's QM plan in accordance with MIL-PRF-38535. The test circuit shall be maintained under document revision level control by the device manufacturer's TRB in accordance with MIL-PRF-38535 and shall be made available to the acquiring or preparing activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in method 1005 of MIL-STD-883.
 - 4.4.3 Group D inspection. The group D inspection end-point electrical parameters shall be as specified in table IIA herein.
- 4.4.4 <u>Group E inspection</u>. Group E inspection is required only for parts intended to be marked as radiation hardness assured (see 3.5 herein).
 - a. End-point electrical parameters shall be as specified in table IIA herein.
 - b. For device classes Q and V, the devices or test vehicle shall be subjected to radiation hardness assured tests as specified in MIL-PRF-38535 for the RHA level being tested. For device class M, the devices shall be subjected to radiation hardness assured tests as specified in MIL-PRF-38535, appendix A for the RHA level being tested. All device classes must meet the postirradiation end-point electrical parameter limits as defined in table I at T_A = +25°C ±5°C, after exposure, to the subgroups specified in table IIA herein.
- 4.6 <u>Programming procedure</u>. The programming procedures shall be as specified by the device manufacturer and shall be made available upon request.
- 4.7 <u>Delta measurements for device class V.</u> Delta measurements, as specified in table IIA, shall be made and recorded before and after the required burn-in screens and steady-state life tests to determine delta compliance. The electrical parameters to be measured, with associated delta limits are listed in table IIB. The device manufacturer may, at his option, either perform delta measurements or within 24 hours after burn-in perform final electrical parameter tests, subgroups 1, 7, and 9
 - 5. PACKAGING
- 5.1 <u>Packaging requirements</u>. The requirements for packaging shall be in accordance with MIL-PRF-38535 for device classes Q and V or MIL-PRF-38535, appendix A for device class M.
 - 6. NOTES
- 6.1 <u>Intended use</u>. Microcircuits conforming to this drawing are intended for use for Government microcircuit applications (original equipment), design applications, and logistics purposes.
- 6.1.1 <u>Replaceability</u>. Microcircuits covered by this drawing will replace the same generic device covered by a contractor prepared specification or drawing.
 - 6.1.2 Substitutability. Device class Q devices will replace device class M devices.
- 6.2 <u>Configuration control of SMD's</u>. All proposed changes to existing SMD's will be coordinated with the users of record for the individual documents. This coordination will be accomplished using DD Form 1692, Engineering Change Proposal.
- 6.3 <u>Record of users</u>. Military and industrial users should inform Defense Supply Center Columbus (DSCC) when a system application requires configuration control and which SMD's are applicable to that system. DSCC will maintain a record of users and this list will be used for coordination and distribution of changes to the drawings. Users of drawings covering microelectronic devices (FSC 5962) should contact DSCC-VA, telephone (614) 692-0544.
- 6.4 <u>Comments</u>. Comments on this drawing should be directed to DSCC-VA, Columbus, Ohio 43218-3990, or telephone (614) 692-0547.

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6.5 Abbreviations, symbols, and definitions.	The abbreviations, symbols	, and definitions used herein are defined in
MIL-PRF-38535 and MIL-HDBK-1331.		

C _{IN}	Input terminal capacitance.
C _{OUT}	
	Ground zero voltage potential.
I _{CC}	Supply current.
I _{II}	Input current.
I _{OZ}	Output current.
T _C	Case temperature.
V _{CC}	

6.5.1 <u>Timing limits</u>. The table of timing values shows either a minimum or a maximum limit for each parameter. Input requirements are specified from the external system point of view. For example, address setup time would be shown as a minimum since the system must supply at least that much time (even though most devices do not require it). On the other hand, responses from the memory are specified from the device point of view. For example, the access time would be shown as a maximum since the device never provides data later than that time.

6.5.2 Waveforms.

WAVEFORM	INPUT	OUTPUT
SYMBOL		
	MUST BE VALID	WILL BE VALID
	CHANGE FROM H TO L	WILL CHANGE FROM H TO L
_/////	CHANGE FROM L TO H	WILL CHANGE FROM L TO H
XXXXXX	DON'T CARE ANY CHANGE PERMITTED	CHANGING STATE UNKNOWN
		HIGH IMPEDANCE

6.6 Sources of supply.

- 6.6.1 <u>Sources of supply for device classes Q and V</u>. Sources of supply for device classes Q and V are listed in QML-38535. The vendors listed in QML-38535 have submitted a certificate of compliance (see 3.6 herein) to DSCC-VA and have agreed to this drawing.
- 6.6.2 <u>Approved sources of supply for device class M.</u> Approved sources of supply for class M are listed in MIL-HDBK-103. The vendors listed in MIL-HDBK-103 have agreed to this drawing and a certificate of compliance (see 3.6 herein) has been submitted to and accepted by DSCC-VA.

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Approved sources of supply for SMD 5962-94717 are listed below for immediate acquisition information only and shall be added to MIL-HDBK-103 and QML-38535 during the next revision. MIL-HDBK-103 and QML-38535 will be revised to include the addition or deletion of sources. The vendors listed below have agreed to this drawing and a certificate of compliance has been submitted to and accepted by DSCC-VA. This information bulletin is superseded by the next dated revision of MIL-HDBK-103 and QML-38535. DSCC maintains an online database of all current sources of supply at http://www.dscc.dla.mil/Programs/Smcr/.

Standard	Vendor	Vendor
microcircuit drawing	CAGE	similar
PIN <u>1</u> /	number	PIN <u>2</u> /
5962-9471701MPA	68994	XC1765DDD8B

- 1/ The lead finish shown for each PIN representing a hermetic package is the most readily available from the manufacturer listed for that part. If the desired lead finish is not listed contact the vendor to determine its availability.
- 2/ Caution. Do not use this number for item acquisition. Items acquired to this number may not satisfy the performance requirements of this drawing.

Vendor CAGEVendor namenumberand address

68994 Xilinx Incorporated 2100 Logic Drive

San Jose, CA 95124

The information contained herein is disseminated for convenience only and the Government assumes no liability whatsoever for any inaccuracies in the information bulletin.